



April 2014

# SSU1N50B

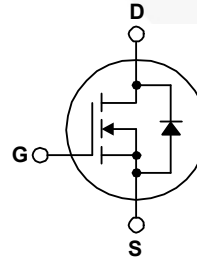
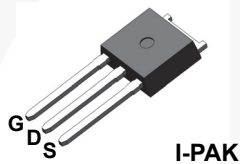
## 520V N-Channel MOSFET

### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies, power factor correction and electronic lamp ballasts based on half bridge.

### Features

- 1.3A, 520V,  $R_{DS(on)} = 5.3\Omega$  @  $V_{GS} = 10\text{ V}$
- Low Gate Charge (Typ. 8.3 nC)
- Low  $C_{rss}$  (Typ. 5.5 pF)
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	SSU1N50BTU	Unit
$V_{DSS}$	Drain-Source Voltage	520	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	1.3	A
		0.82	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	5.0	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	100	mJ
$I_{AR}$	Avalanche Current (Note 1)	1.3	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	2.6	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
$P_D$	Power Dissipation ( $T_A = 25^\circ\text{C}$ ) *	2.5	W
	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	26	W
		0.21	W/ $^\circ\text{C}$
$T_J, T_{stg}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	SSU1N50BTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.76	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max	50	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Minimum Pad of 2-oz Copper), Max.	110	$^\circ\text{C}/\text{W}$

SSU1N50B - N-Channel B-FET MOSFET

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
SSU1N50BTU	SSU1N50B	I-PAK	Tube	N/A	N/A	70 units

## Electrical Characteristics

 $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	520	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.54	--	V/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.65\text{ A}$	--	4.1	5.3	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 0.65\text{ A}$	--	1.65	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	260	340	pF
$C_{oss}$	Output Capacitance		--	25	33	pF
$C_{riss}$	Reverse Transfer Capacitance		--	5.5	7.2	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{ V}, I_D = 1.5\text{ A},$ $R_G = 25\ \Omega$	--	14	40	ns
$t_r$	Turn-On Rise Time		--	40	90	ns
$t_{d(off)}$	Turn-Off Delay Time		--	35	80	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	35	80
$Q_g$	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 1.5\text{ A},$ $V_{GS} = 10\text{ V}$	--	8.3	11	nC
$Q_{gs}$	Gate-Source Charge		--	1.5	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	3.4	--

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	1.3	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	5.0	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.3\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 1.5\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	230	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	0.94	--	$\mu\text{C}$

#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2.  $L = 106\text{mH}, I_{AS} = 1.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 1.5\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature.

Typical Characteristics

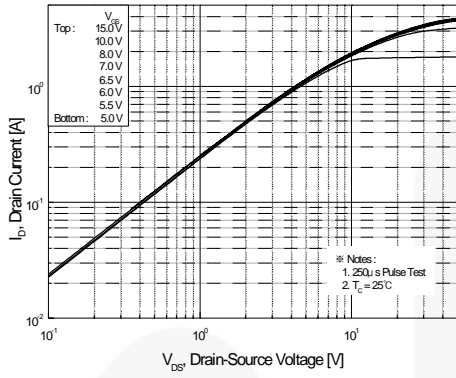


Figure 1. On-Region Characteristics

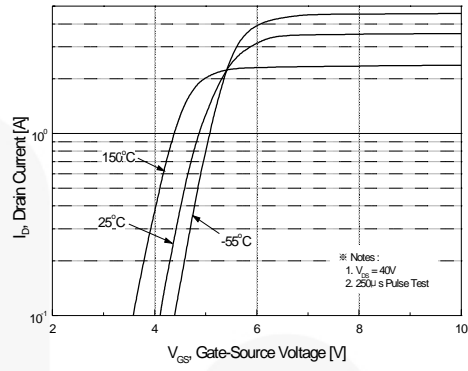


Figure 2. Transfer Characteristics

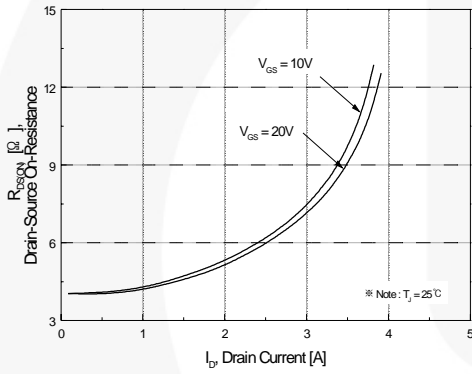


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

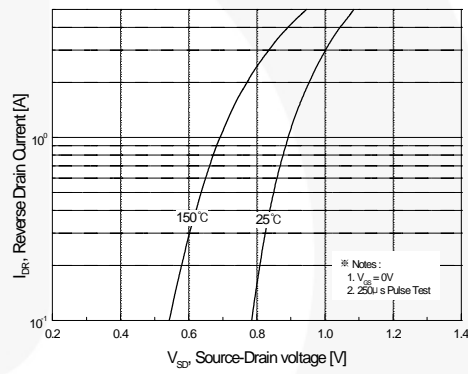


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

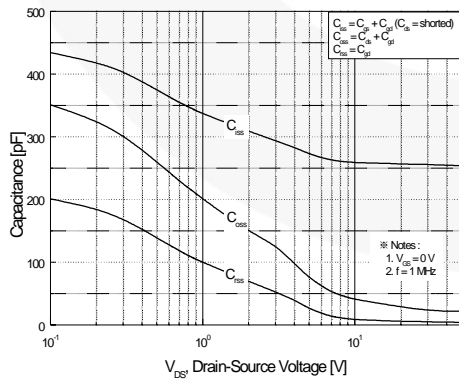


Figure 5. Capacitance Characteristics

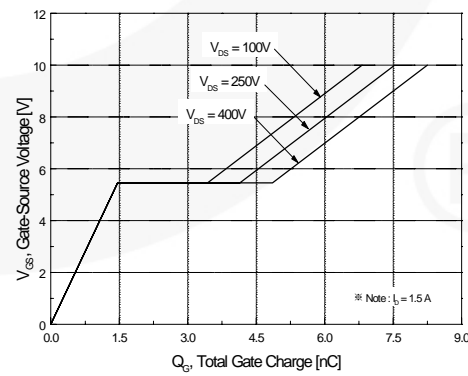


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

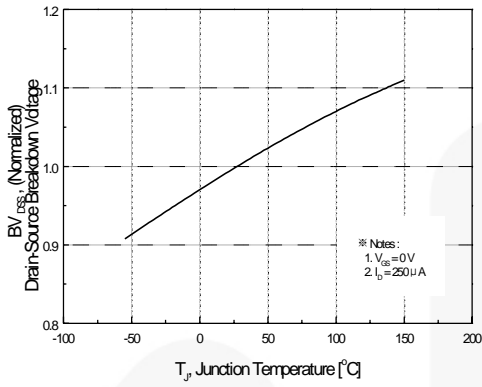


Figure 7. Breakdown Voltage Variation vs Temperature

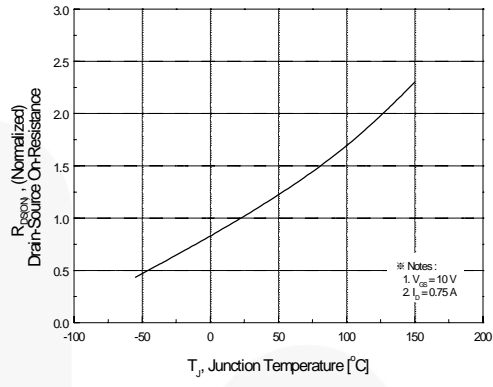


Figure 8. On-Resistance Variation vs Temperature

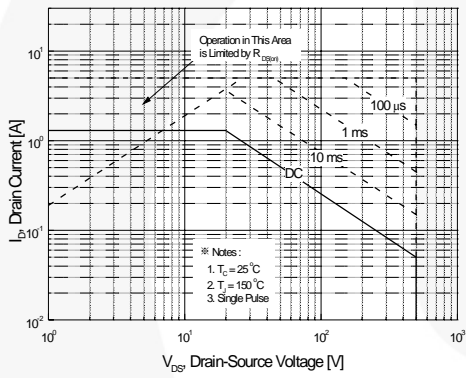


Figure 9. Maximum Safe Operating Area

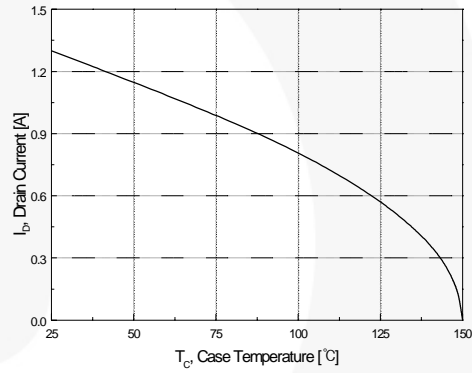


Figure 10. Maximum Drain Current vs Case Temperature

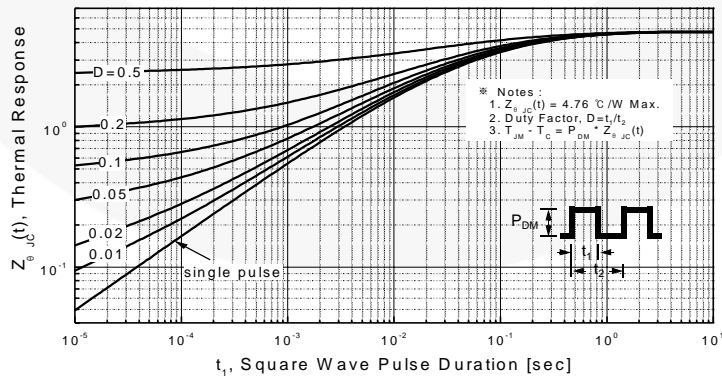


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

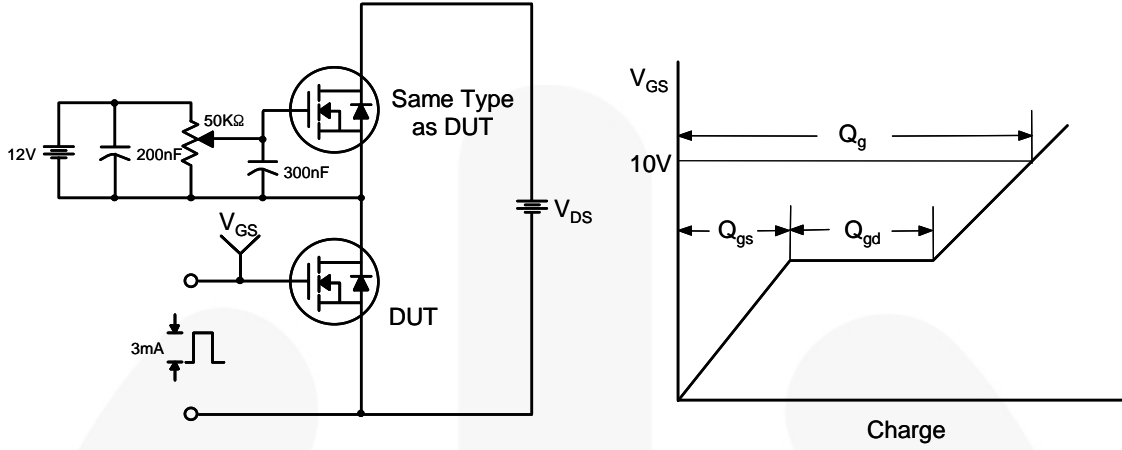


Figure 13. Resistive Switching Test Circuit & Waveforms

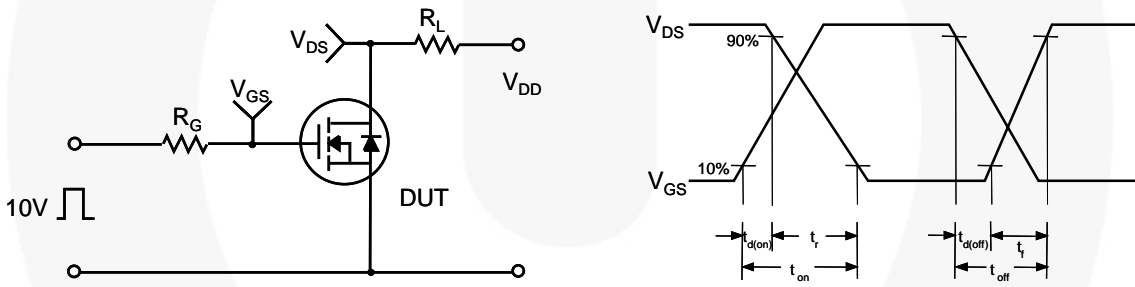


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

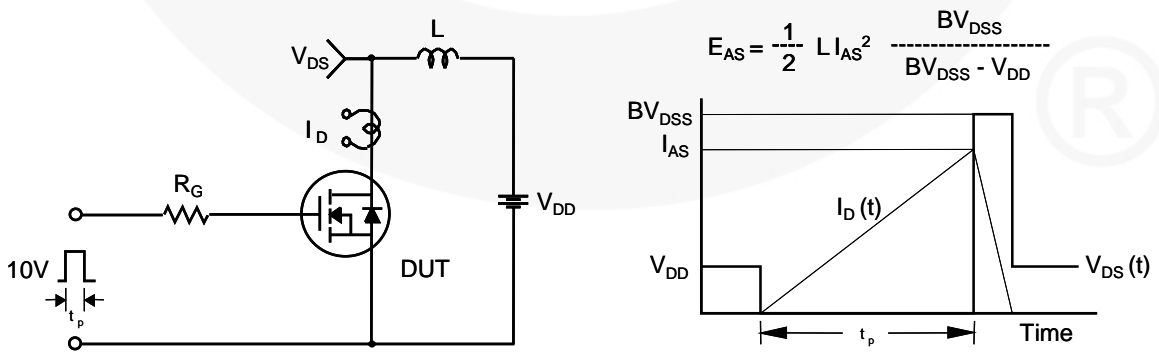
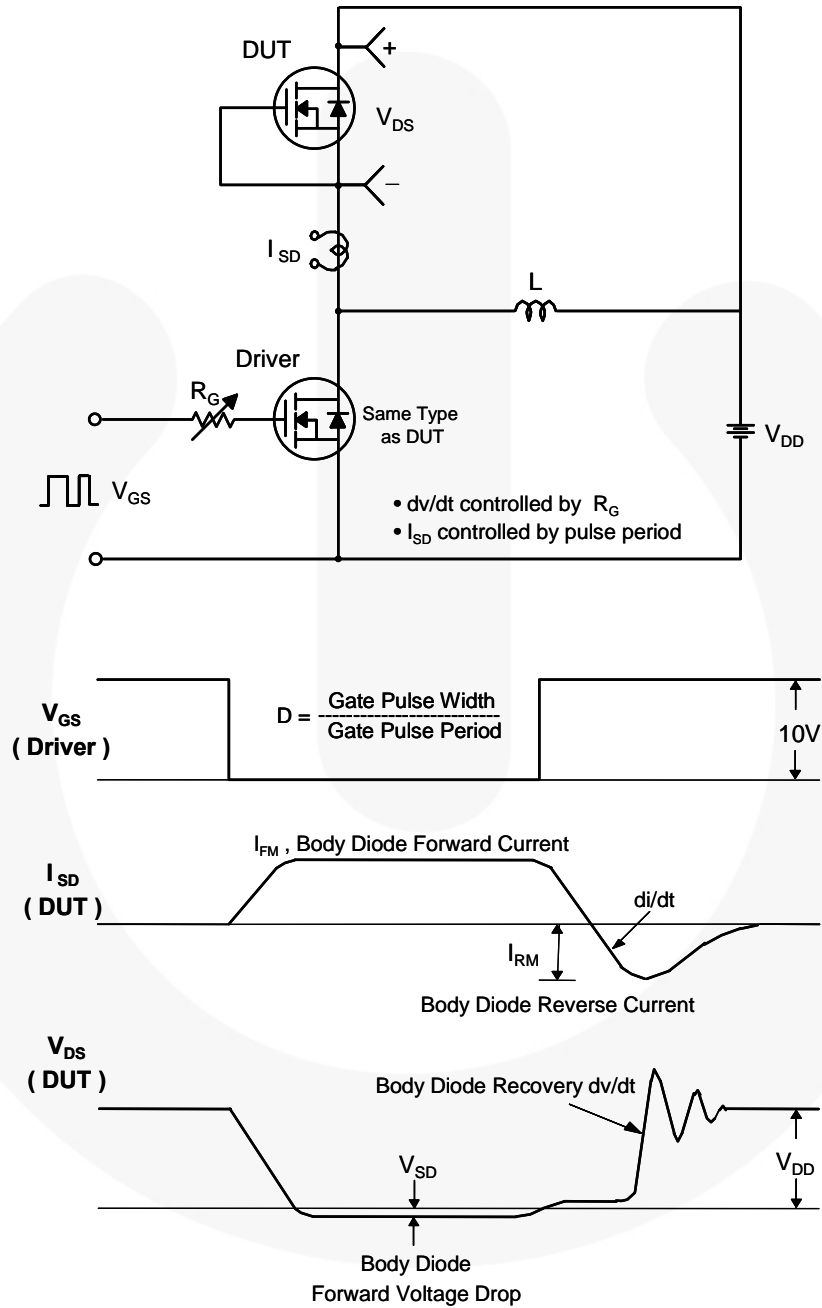
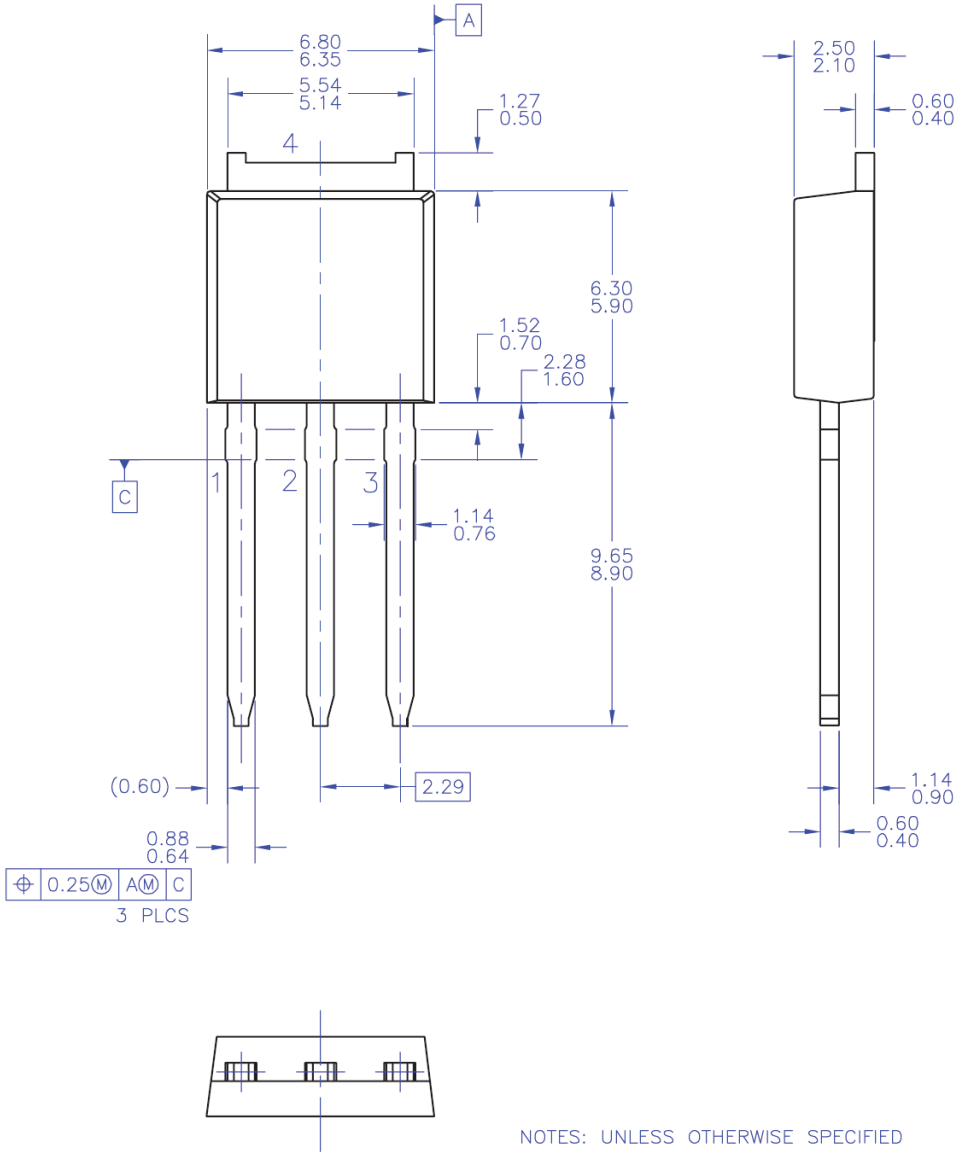


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



**Mechanical Dimensions**



TO251A03REVA

NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) THIS PACKAGE CONFORMS TO JEDEC, TO-251, ISSUE C, VARIATION AA, DATED SEP 1988.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

**Figure 16. TO251 (I-PAK), Molded, 3-Lead**

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| BitSiC™                  | Global Power ResourceSM | Programmable Active Droop™                      | TinyBuck™        |
| Build it Now™            | GreenBridge™            | QFET®   | TinyCalc™        |
| CorePLUS™                | Green FPS™              | QS™   | TinyLogic®       |
| CorePOWER™               | Green FPS™ e-Series™    | Quiet Series™                                   | TINYOPTO™        |
| CROSSVOLT™               | Gmax™                   | RapidConfigure™                                 | TinyPower™       |
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